

**AMENDMENTS TO THE CLAIMS**

**IN THE CLAIMS:**

Please **AMEND** claims 1 and 5 as shown below.

A copy of all pending claims and a status of the claims is provided below.

1. (Currently Amended) A switching device of an X-ray sensor which comprises  
a thin film transistor (TFT) provided on a transparent substrate,  
a first protecting insulation layer which covers the TFT,  
storage capacity electrodes electrically isolated from a gate line and a terminal portion of the TFT, and connected to a ground wire formed on a gate insulating layer ~~on the first protecting insulation layer,~~  
a second protecting insulation layer which covers the storage capacity electrodes formed on the first protecting insulation layer, and  
a pixel electrode connected to one terminal of the TFT on the second protecting insulation layer,  
at least one portion of the storage capacity electrodes shielding the TFT.
2. (Original) A switching device according to claim 1, wherein the ground wire is connected by a contact hole which is formed at a lower portion of the first protecting insulation layer and penetrates the first protecting insulation layer.
3. (Original) A switching device according to claim 1, wherein the pixel electrode is connected to one terminal of the TFT through a contact hole which penetrates the first protecting insulation layer and the second protecting insulation layer.
4. (Original) A switching device according to claim 1, wherein the first protecting insulation layer and the second protecting insulation layer are formed of an inorganic insulation layer.

5. (Currently Amended) A method for manufacturing a switching device of an X-ray sensor which comprises the steps of:

- forming a TFT and a ground wire on a transparent substrate;
- forming a first protecting insulation layer which covers the TFT and the ground wire;
- forming a first contact hole on the ground wire section and patterning storage capacity electrodes connected to the ground wire on the first protecting insulation layer such that at least a portion of the storage capacity electrodes shields the TFT, and such that the storage capacity electrodes are electrically isolated from a gate line and a terminal portion of the TFT;
- forming a second protecting insulation layer on the first protecting insulation layer formed by patterning the storage capacity electrodes; and
- forming a second contact hole on one terminal portion of the TFT and forming a pixel electrode connected to one terminal of the TFT on the second protecting insulation layer.

6. (Original) A method according to claim 5, wherein the contact hole is formed such that a portion of one terminal of the TFT is simultaneously exposed when the first contact hole is formed and the pixel electrode makes contact with one terminal of the TFT through the contact hole and the second contact hole.

7. (Cancelled).

8. (Previously Amended) A method according to claim 5, wherein the first protecting insulation layer and the second protecting insulation layer are formed of an inorganic insulation.